



## **2SA1020** TRANSISTOR (PNP)

## **FEATURES**

Power dissipation

mW (Tamb=25°C)  $P_{CM}$ : 900

Collector current

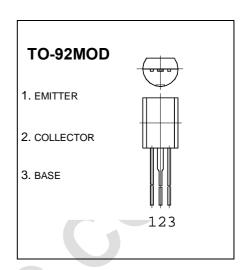
: -2  $I_{CM}$ 

Collector-base voltage

V<sub>(BR)CBO</sub>: -50

Operating and storage junction temperature range

T<sub>J</sub>, T<sub>stg</sub>: -55℃ to +150℃



## **ELECTRICAL CHARACTERISTICS (Tamb=25℃** unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	Ic=-100μA, I <sub>E</sub> =0	-50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	Ic=-1mA, I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100 μA, I <sub>C</sub> =0	-5			٧
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50 V, I <sub>E</sub> =0			-1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB}$ =-5 V, $I_{C}$ =0			-1	μΑ
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-2 V, I <sub>C</sub> =-500 A	70		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1A, I <sub>B</sub> =-50 mA			-0.5	<b>V</b>
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-1 A, I <sub>B</sub> =-50 mA			-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-2 V, I <sub>C</sub> =-500 mA		100		MHz

## CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	0	Y
Range	70-140	120-240